

# Trench gate field-stop IGBT 1200V M series



## New M series IGBTs increase energy efficiency and ruggedness for solar and industrial power applications

Based on the third generation at 1200 V for IGBTs in ST's proprietary trench gate field-stop technology, the M series increases the efficiency of UPS, solar, welding and industrial drive applications. Working up to 20 kHz in hard-switching topologies thanks to the optimal trade-off between on state conduction and switching performance, these devices also offers outstanding robustness and EMI characteristics.



### KEY FEATURES

- 10  $\mu$ s minimum short circuit capability at starting  $T_J$  of 150°C
- 175 °C maximum operating junction temperature ( $T_J$ )
- The lowest overall losses up to 20 kHz

### KEY BENEFITS

- M series is tailored to improve efficiency of targeted applications
- Longer lifetime
- Safe paralleling
- Soft and fast recovery antiparallel diode
- High robustness

### MAIN APPLICATIONS

- Motor Control
- Industrial drives
- UPS
- Solar inverters
- Welding

## 1200V M SERIES IGBTs

### STGW40M120DF3 OUTPUT CHARACTERISTICS AND SWITCHING OFF

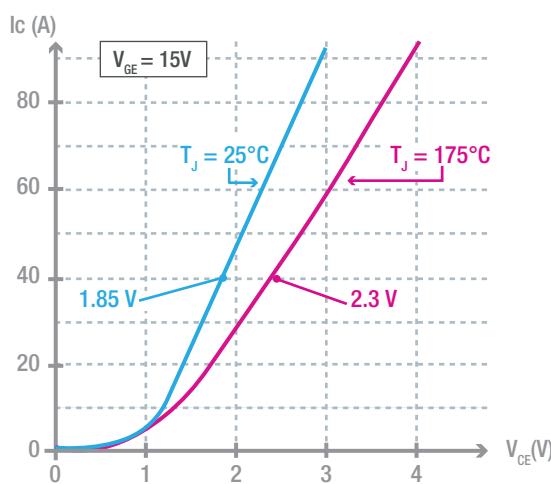
The typical output characteristics and switching-off are showed below.

On the left, the typical output characteristics for the STGWA40M120DF3 at both 25°C and 175°C. As shown below a positive derating of  $V_{CE(sat)}$  is resulting: from 1.85V at 25°C to 2.3V at 175°C.

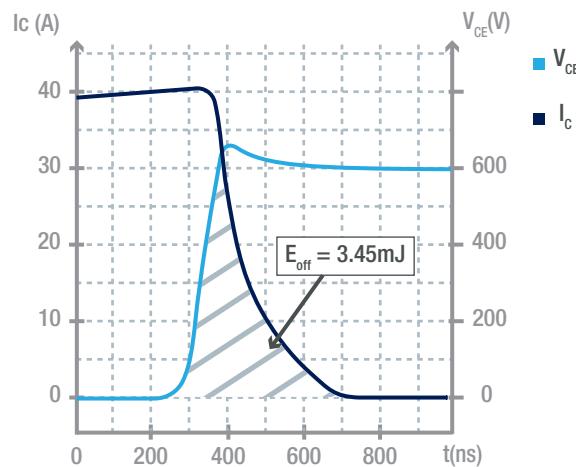
On the right, the typical switching-off is showed. Despite the extremely high temperature of 175°C, the switching-off loss are limited and no important tail current is resulting. This to show the best compromise between conduction and switching ideal for any industrial drive applications working up to 20 kHz in hard-switching circuitries.

### TYPICAL CURVES

Output Characteristics



Turn-off at  $T_J = 175^\circ\text{C}$   
 $V_{CC} = 600\text{V}$ ,  $R_G = 10\Omega$ ,  $I_C = 40\text{A}$ ,  $V_{GE} = 15/0\text{V}$



### DEVICE SUMMARY

IGBT P/Ns	BVces	$I_{CN}^1)$	$V_{ce(sat)}^2)$	$E_{on}^3)$	$E_{off}^3)$	$t_{sc}^4)$	Max. operating $T_J$	Package	
								TO-247	TO-247 LL
STGx8M120DF3	1200	8	1.85	0.39	0.37	10	175	W	WA
		15		0.55	0.85			W	WA
		25		0.85	1.3			W	WA
		40		1.5	2.25			W	WA

1)  $I_{CN}$ : Nominal collector current @  $T_J = 100^\circ\text{C}$

2)  $V_{ce(sat)}$ : Typical conduction losses @  $I_{CN}$ ,  $T_J = 25^\circ\text{C}$

3)  $E_{on}$  /  $E_{off}$ : Typical switching energy losses @  $I_{CN}$ ,  $T_J = 25^\circ\text{C}$ ,  $V_{CC} = 600\text{V}$

4)  $t_{sc}$ : min short circuit withstand time @  $V_{CC} \leq 600\text{V}$ ,  $T_{start} \leq 150^\circ\text{C}$ ,  $V_{GE} = 15\text{V}$

For more information on IGBT products and solution download and consult the APP ST-IGBT-Finder



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